

74HC423; 74HCT423

Dual retriggerable monostable multivibrator with reset

Rev. 03 — 24 July 2008

Product data sheet

1. General description

74HC423; 74HCT423 are high-speed Si-gate CMOS devices that are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC423; 74HCT423 dual retriggerable monostable multivibrator with reset has two methods of output pulse width control.

1. The minimum pulse width is essentially determined by the selection of an external resistor (R_{EXT}) and capacitor (C_{EXT}), see [Section 12.1](#).
2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input ($n\bar{A}$) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period ($nQ = \text{HIGH}$, $n\bar{Q} = \text{LOW}$) can be made as long as desired. When $n\bar{RD}$ is LOW, it forces the nQ output LOW, the $n\bar{Q}$ output HIGH and also inhibits the triggering. [Figure 10](#) and [Figure 11](#) illustrate pulse control by reset.

The $n\bar{A}$ and nB inputs' Schmitt trigger action makes them highly tolerant to slower input rise and fall times.

The 74HC423; 74HCT423 are identical to the 74HC123; 74HCT123 except that they cannot be triggered via the reset input.

2. Features

- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100% duty factor
- Direct reset terminates output pulse
- Schmitt-trigger action on all inputs except for the reset input
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

| Type number | Package | | | Version |
|-------------|-------------------|----------|--|----------|
| | Temperature range | Name | Description | |
| 74HC423N | -40 °C to +125 °C | DIP16 | plastic dual in-line package; 16 leads (300 mil) | SOT38-4 |
| 74HCT423N | | | | |
| 74HC423D | -40 °C to +125 °C | SO16 | plastic small outline package; 16 leads; body width 3.9 mm | SOT109-1 |
| 74HCT423D | | | | |
| 74HC423BQ | -40 °C to +125 °C | DHVQFN16 | plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm | SOT763-1 |
| 74HCT423BQ | | | | |
| 74HCT423DB | -40 °C to +125 °C | SSOP16 | plastic shrink small outline package; 16 leads; body width 5.3 mm | SOT338-1 |
| 74HCT423PW | -40 °C to +125 °C | TSSOP16 | plastic thin shrink small outline package; 16 leads; body width 4.4 mm | SOT403-1 |

4. Functional diagram

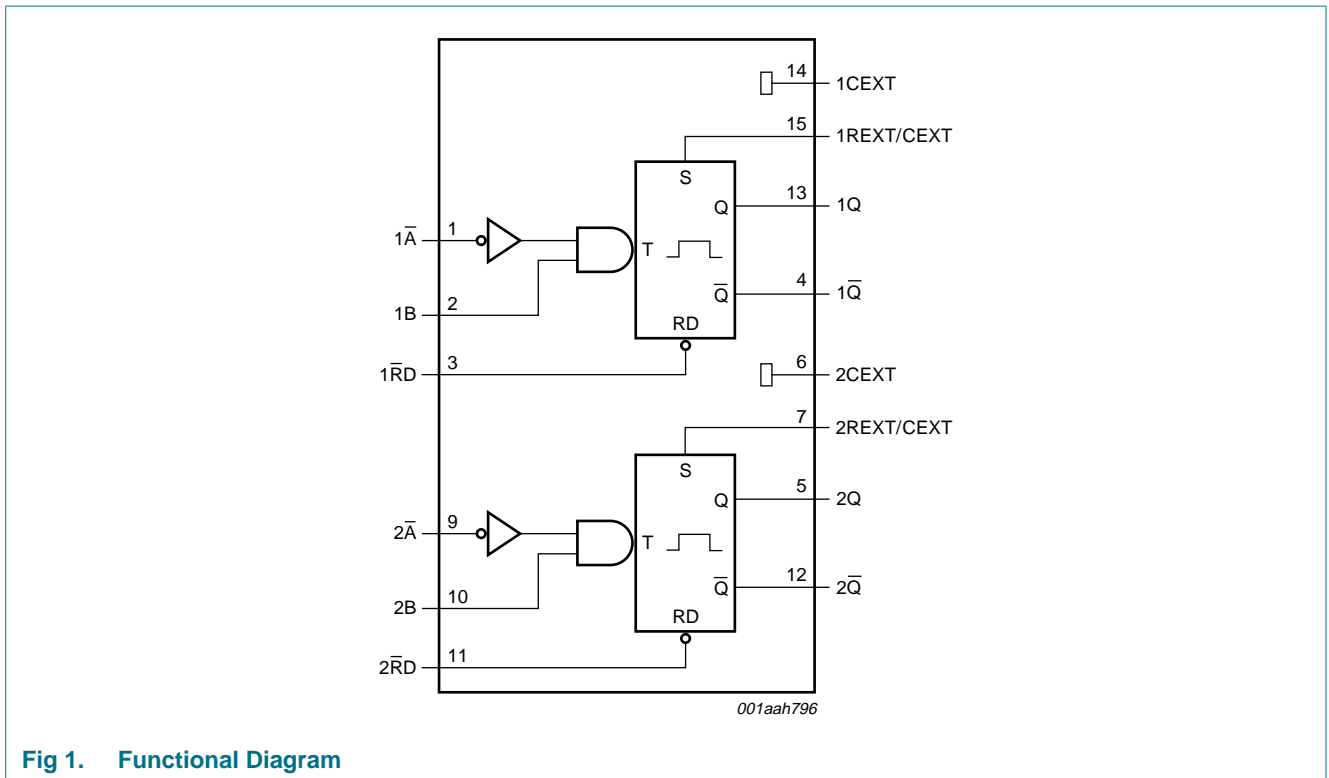


Fig 1. Functional Diagram

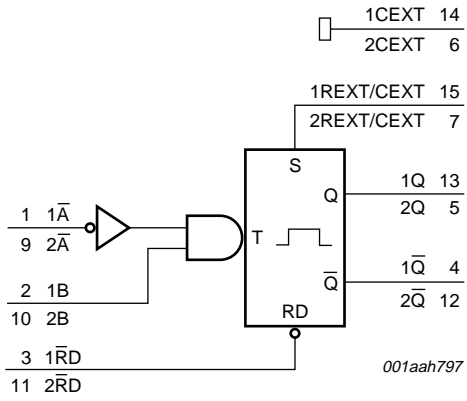


Fig 2. Logic symbol

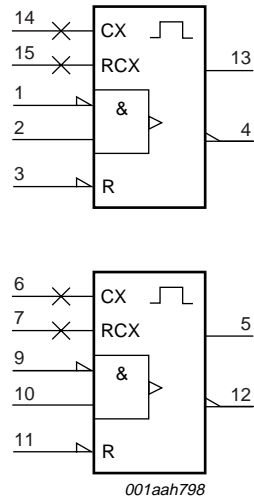


Fig 3. IEC Logic symbol

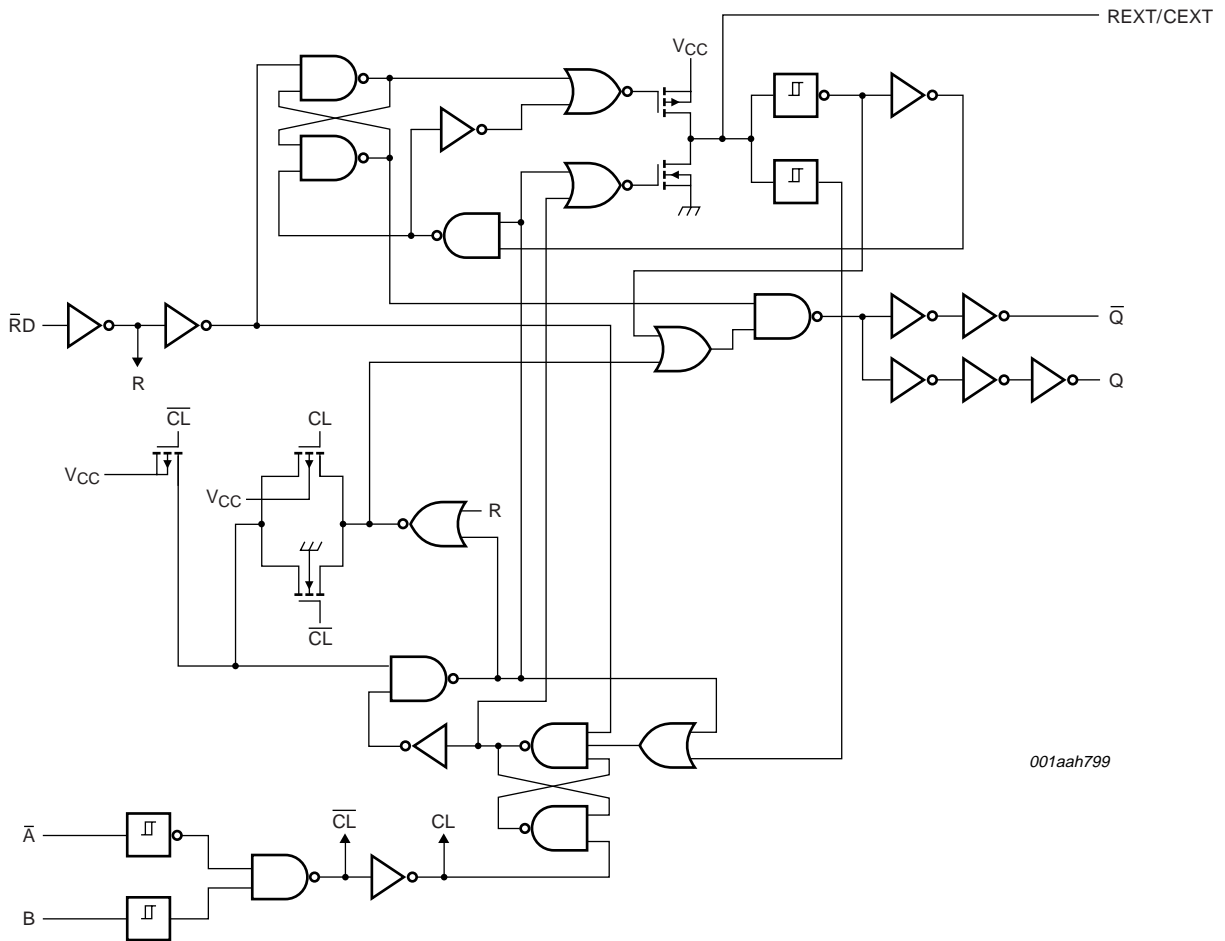
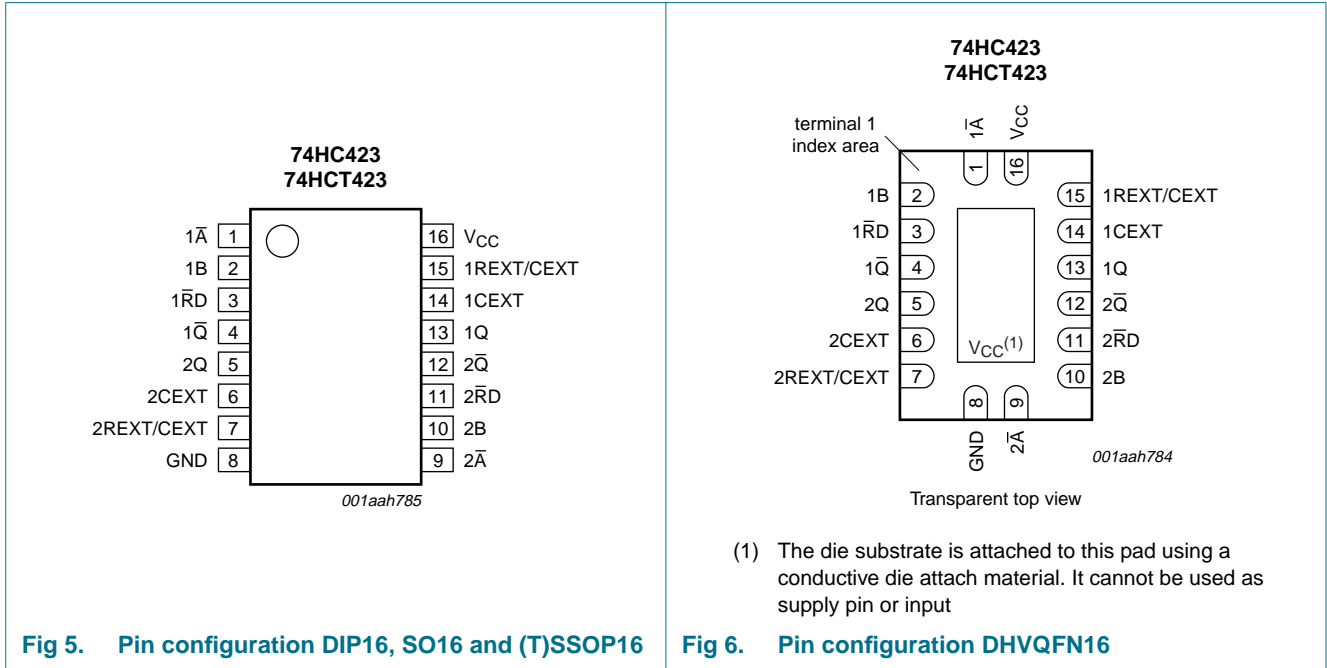


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning







5.2 Pin description

Table 2. Pin description


| Symbol | Pin | Description |
|-----------------------------|-------|---|
| 1 \bar{A} , 2 \bar{A} | 1, 9 | trigger input (negative edge triggered) |
| 1B, 2B | 2, 10 | trigger input (positive edge triggered) |
| 1 $\bar{R}D$, 2 $\bar{R}D$ | 3, 11 | direct reset (active LOW) |
| 1 \bar{Q} , 2 \bar{Q} | 4, 12 | output (active LOW) |
| GND | 8 | ground (0 V) |
| 1Q, 2Q | 13, 5 | output (active HIGH) |
| 1CEXT, 2CEXT | 14, 6 | external capacitor connection |
| 1REXT/CEXT, 2REXT/CEXT | 15, 7 | external resistor/capacitor connection |
| V _{CC} | 16 | supply voltage |


6. Functional description

Table 3. Function table^[1]

| Input | | | Output | |
|-------|----|----|---|---|
| nRD | nA | nB | nQ | nQ |
| L | X | X | L | H |
| X | H | X | L ^[2] | H ^[2] |
| X | X | L | L ^[2] | H ^[2] |
| H | L | ↑ |  |  |
| H | ↓ | H |  |  |

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 ↑ = LOW-to-HIGH transition;
 ↓ = HIGH-to-LOW transition;

 = one HIGH level output pulse;

 = one LOW level output pulse.

- [2] If the monostable multivibrator was triggered before this condition was established, the pulse will continue as programmed.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---|------------------|------|------|
| V _{CC} | supply voltage | | -0.5 | +7 | V |
| I _{IK} | input clamping current | V _I < -0.5 V or V _I > V _{CC} + 0.5 V | ^[1] - | ±20 | mA |
| I _{OK} | output clamping current | V _O < -0.5 V or V _O > V _{CC} + 0.5 V | ^[1] - | ±20 | mA |
| I _O | output current | -0.5 V < V _O < V _{CC} + 0.5 V | - | ±25 | mA |
| I _{CC} | supply current | | - | 50 | mA |
| I _{GND} | ground current | | -50 | - | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| P _{tot} | total power dissipation | DIP16 package | ^[2] - | 750 | mW |
| | | SO16, SSOP16, TSSOP16 and DHVQFN16 packages | ^[3] - | 500 | mW |

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

- [2] For DIP16 packages: above 70 °C the value of P_{tot} derates linearly at 12 mW/K.

- [3] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K;
 For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K;
 For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 74HC423 | | | 74HCT423 | | | Unit |
|------------------|-------------------------------------|-------------------------|---------|------|-----------------|----------|------|-----------------|------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| V _{CC} | supply voltage | | 2.0 | 5.0 | 6.0 | 4.5 | 5.0 | 5.5 | V |
| V _I | input voltage | | 0 | - | V _{CC} | 0 | - | V _{CC} | V |
| V _O | output voltage | | 0 | - | V _{CC} | 0 | - | V _{CC} | V |
| T _{amb} | ambient temperature | | -40 | - | +125 | -40 | - | +125 | °C |
| Δt/ΔV | input transition rise and fall rate | V _{CC} = 2.0 V | - | - | 625 | - | - | - | ns/V |
| | | V _{CC} = 4.5 V | - | 1.67 | 139 | - | 1.67 | 139 | ns/V |
| | | V _{CC} = 6.0 V | - | - | 83 | - | - | - | ns/V |

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|-----------------|---------------------------|--|----------------|--|------|------------------|------|-------------------|------|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| 74HC423 | | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | 1.5 | 1.2 | - | 1.5 | - | 1.5 | - | V |
| | | V _{CC} = 4.5 V | 3.15 | 2.4 | - | 3.15 | - | 3.15 | - | V |
| | | V _{CC} = 6.0 V | 4.2 | 3.2 | - | 4.2 | - | 4.2 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | 0.8 | 0.5 | - | 0.5 | - | 0.5 | V |
| | | V _{CC} = 4.5 V | - | 2.1 | 1.35 | - | 1.35 | - | 1.35 | V |
| | | V _{CC} = 6.0 V | - | 2.8 | 1.8 | - | 1.8 | - | 1.8 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = -20 μA; V _{CC} = 2.0 V | 1.9 | 2.0 | - | 1.9 | - | 1.9 | - | V |
| | | I _O = -20 μA; V _{CC} = 4.5 V | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -20 μA; V _{CC} = 6.0 V | 5.9 | 6.0 | - | 5.9 | - | 5.9 | - | V |
| | | I _O = -4.0 mA; V _{CC} = 4.5 V | 3.98 | 4.32 | - | 3.84 | - | 3.7 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = 20 μA; V _{CC} = 2.0 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 20 μA; V _{CC} = 4.5 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 20 μA; V _{CC} = 6.0 V | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 4.5 V | - | 0.15 | 0.26 | - | 0.33 | - | 0.4 | V |
| I _I | input leakage current | V _I = V _{CC} or GND; V _{CC} = 6.0 V | - | - | ±0.1 | - | ±1.0 | - | ±1.0 | μA |
| | | I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V | - | - | 8.0 | - | 80 | - |

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|-----------------|---------------------------|---|-------|------|-----------|------------------|-----------|-------------------|-----------|---------------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| C_I | input capacitance | | - | 3.5 | - | - | - | - | - | pF |
| 74HCT423 | | | | | | | | | | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | 2.0 | 1.6 | - | 2.0 | - | 2.0 | - | V |
| V_{IL} | LOW-level input voltage | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | - | 1.2 | 0.8 | - | 0.8 | - | 0.8 | V |
| V_{OH} | HIGH-level output voltage | $V_I = V_{IH}\text{ or }V_{IL}; V_{CC} = 4.5\text{ V}$ | | | | | | | | |
| | | $I_O = -20\ \mu\text{A}$ | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | $I_O = -4.0\text{ mA}$ | 3.98 | 4.32 | - | 3.84 | - | 3.7 | - | V |
| V_{OL} | LOW-level output voltage | $V_I = V_{IH}\text{ or }V_{IL}; V_{CC} = 4.5\text{ V}$ | | | | | | | | |
| | | $I_O = 20\ \mu\text{A}$ | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | $I_O = 4.0\text{ mA}$ | - | 0.15 | 0.26 | - | 0.33 | - | 0.4 | V |
| I_I | input leakage current | $V_I = V_{CC}\text{ or GND}; V_{CC} = 5.5\text{ V}$ | - | - | ± 0.1 | - | ± 1.0 | - | ± 1.0 | μA |
| I_{CC} | supply current | $V_I = V_{CC}\text{ or GND}; V_{CC} = 5.5\text{ V}; I_O = 0\text{ A}$ | - | - | 8.0 | - | 80 | - | 160 | μA |
| ΔI_{CC} | additional supply current | per input pin; $V_I = V_{CC} - 2.1\text{ V};$ other inputs at $V_{CC}\text{ or GND};$ $V_{CC} = 4.5\text{ V to }5.5\text{ V}; I_O = 0\text{ A}$ | | | | | | | | |
| | | \overline{nA}, nB inputs | - | 35 | 126 | - | 158 | - | 172 | μA |
| | | $n\overline{RD}$ input | - | 50 | 180 | - | 225 | - | 245 | μA |
| C_I | input capacitance | | - | 3.5 | - | - | - | - | - | pF |

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; test circuit see Figure 12.

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit | |
|-------------------|-------------------|---|-------|-----|-----|------------------|-----|-------------------|-----|------|---------|
| | | | Min | Typ | Max | Min | Max | Min | Max | | |
| 74HC423 | | | | | | | | | | | |
| t _{pd} | propagation delay | n \bar{A} or nB to nQ or n \bar{Q} ; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; see Figure 7 | [1] | | | | | | | | |
| | | V _{CC} = 2.0 V | - | 80 | 255 | - | 320 | - | 385 | ns | |
| | | V _{CC} = 4.5 V | - | 29 | 51 | - | 64 | - | 77 | ns | |
| | | V _{CC} = 5.0 V; C _L = 15 pF | - | 25 | - | - | - | - | - | ns | |
| | | V _{CC} = 6.0 V | - | 23 | 43 | - | 54 | - | 65 | ns | |
| | | n $\bar{R}D$ to nQ or n \bar{Q} ; see Figure 7 | [1] | | | | | | | | |
| | | V _{CC} = 2.0 V | - | 66 | 215 | - | 270 | - | 325 | ns | |
| | | V _{CC} = 4.5 V | - | 24 | 43 | - | 54 | - | 65 | ns | |
| t _t | transition time | see Figure 7 | [2] | | | | | | | | |
| | | V _{CC} = 2.0 V | - | 19 | 75 | - | 95 | - | 110 | ns | |
| | | V _{CC} = 4.5 V | - | 7 | 15 | - | 19 | - | 22 | ns | |
| | | V _{CC} = 6.0 V | - | 6 | 13 | - | 16 | - | 19 | ns | |
| t _w | pulse width | n \bar{A} input LOW; see Figure 7 and Figure 8 | | | | | | | | | |
| | | V _{CC} = 2.0 V | 100 | 11 | - | 125 | - | 150 | - | ns | |
| | | V _{CC} = 4.5 V | 20 | 4 | - | 25 | - | 30 | - | ns | |
| | | V _{CC} = 6.0 V | 17 | 3 | - | 21 | - | 26 | - | ns | |
| | | nB input HIGH; see Figure 7 and Figure 8 | | | | | | | | | |
| | | V _{CC} = 2.0 V | 100 | 17 | - | 125 | - | 150 | - | ns | |
| | | V _{CC} = 4.5 V | 20 | 6 | - | 25 | - | 30 | - | ns | |
| | | V _{CC} = 6.0 V | 17 | 5 | - | 21 | - | 26 | - | ns | |
| | | n $\bar{R}D$ input LOW; see Figure 7 and Figure 8 | | | | | | | | | |
| | | V _{CC} = 2.0 V | 100 | 14 | - | 125 | - | 150 | - | ns | |
| | | V _{CC} = 4.5 V | 20 | 5 | - | 25 | - | 30 | - | ns | |
| | | V _{CC} = 6.0 V | 17 | 4 | - | 21 | - | 26 | - | ns | |
| | | nQ HIGH or n \bar{Q} LOW; V _{CC} = 5.0 V; R _{EXT} = 10 k Ω ; C _{EXT} = 100 nF; see Figure 7 and Figure 8 | | | 450 | - | - | - | - | - | μ s |
| | | nQ HIGH or n \bar{Q} LOW; V _{CC} = 5.0 V; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; V _I = GND to V _{CC} ; see Figure 7 and Figure 8 | [3] | - | 75 | - | - | - | - | - | ns |
| t _{trig} | retrigger time | n \bar{A} or nB input; V _{CC} = 5.0 V; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; see Figure 10 | [4] | - | 110 | - | - | - | - | ns | |

Table 7. Dynamic characteristics ...continued
GND = 0 V; test circuit see Figure 12.

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|------------------|-------------------------------|--|-----------|-----|------|------------------|-----|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| R _{EXT} | external timing resistor | V _{CC} = 2.0 V; see Figure 8 | 10 | - | 1000 | - | - | - | - | kΩ |
| | | V _{CC} = 5.0 V | 2 | - | 1000 | - | - | - | - | kΩ |
| C _{EXT} | external timing capacitor | V _{CC} = 5.0 V; see Figure 8 | no limits | | | | | | pF | |
| C _{PD} | power dissipation capacitance | per package; V _I = GND to V _{CC} | - | 54 | - | - | - | - | - | pF |

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| | | | | | | | | | | | |
|-------------------|---------------------------|---|-----|-----------|-----|------|----|----|----|----|----|
| t _{pd} | propagation delay | n \bar{A} or nB to nQ or n \bar{Q} ; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; see Figure 7 | | | | | | | | | |
| | | V _{CC} = 4.5 V | [1] | - | 30 | 51 | - | 64 | - | 77 | ns |
| | | V _{CC} = 5.0 V; C _L = 15 pF | [1] | - | 26 | - | - | - | - | - | ns |
| | | n \bar{RD} to nQ or n \bar{Q} ; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; see Figure 7 | [1] | - | 26 | 48 | - | 60 | - | 72 | ns |
| | | V _{CC} = 4.5 V | [1] | - | 26 | 48 | - | 60 | - | 72 | ns |
| | | V _{CC} = 5.0 V; C _L = 15 pF | [1] | - | 22 | - | - | - | - | ns | |
| t _t | transition time | V _{CC} = 4.5 V; Figure 7 | [2] | - | 7 | 15 | - | 19 | - | 22 | ns |
| t _w | pulse width | trigger pulse; n \bar{A} input LOW; V _{CC} = 4.5 V; see Figure 7 and Figure 10 | | 20 | 5 | - | 25 | - | 30 | - | ns |
| | | trigger pulse; nB input HIGH; V _{CC} = 4.5 V; see Figure 7 and Figure 10 | | 20 | 5 | - | 25 | - | 30 | - | ns |
| | | reset pulse; n \bar{RD} input LOW; V _{CC} = 4.5 V; see Figure 7 and Figure 11 | | 20 | 7 | - | 25 | - | 30 | - | ns |
| | | output pulse; nQ HIGH or n \bar{Q} LOW; V _{CC} = 5.0 V; R _{EXT} = 10 kΩ; C _{EXT} = 100 nF; see Figure 7, Figure 10 and Figure 11 | | - | 450 | - | - | - | - | - | μs |
| | | output pulse; nQ HIGH or n \bar{Q} LOW; V _{CC} = 5.0 V; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; V _I = GND to V _{CC} - 1.5 V; see Figure 7, Figure 10 and Figure 11 | [3] | - | 75 | - | - | - | - | - | ns |
| t _{trig} | retrigger time | n \bar{A} or nB input; V _{CC} = 5.0 V; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; see Figure 10 | | - | 110 | - | - | - | - | ns | |
| R _{EXT} | external timing resistor | V _{CC} = 5.0 V; see Figure 8 | | 2 | - | 1000 | - | - | - | kΩ | |
| C _{EXT} | external timing capacitor | V _{CC} = 5.0 V; see Figure 8 | [5] | no limits | | | | | | pF | |

Table 7. Dynamic characteristics ...continued

GND = 0 V; test circuit see [Figure 12](#).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|-----------------|-------------------------------|--|-------|-----|-----|------------------|-----|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| C _{PD} | power dissipation capacitance | per package; V _I = GND to V _{CC} - 1.5 V [6] | - | 56 | - | - | - | - | - | pF |

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_t is the same as t_{THL} and t_{TLH}.

[3] For other R_{EXT} and C_{EXT} combinations see [Figure 8](#). If C_{EXT} > 10 pF, the next formula is valid:

t_W = K × R_{EXT} × C_{EXT} (typ.), where:

t_W = output pulse width in ns;

R_{EXT} = external resistor in kΩ;

C_{EXT} = external capacitor in pF;

K = 0.55 for V_{CC} = 2.0 V and 0.45 for V_{CC} = 5.0 V; see [Figure 9](#).

Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[4] The time to retrigger the monostable multivibrator depends on the values of R_{EXT} and C_{EXT}. The output pulse width will only be extended when the time between the active-going edges of the trigger input pulses meets the minimum retrigger time.

If C_{EXT} > 10 pF, the next formula (at V_{CC} = 5.0 V) for the set-up time of a retrigger pulse is valid:

t_{trig} = 30 + 0.19 × R_{EXT} × C_{EXT}^{0.9} + 13 × R_{EXT}^{1.05} (typ.); where:

t_{trig} = retrigger time in ns;

C_{EXT} = external capacitor in pF;

R_{EXT} = external resistor in kΩ.

Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[5] When the device is powered-up, initiate the device via a reset pulse, when C_{EXT} < 50 pF.

[6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

P_D = C_{PD} × V_{CC}² × f_i × N + ∑ (C_L × V_{CC}² × f_o); where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

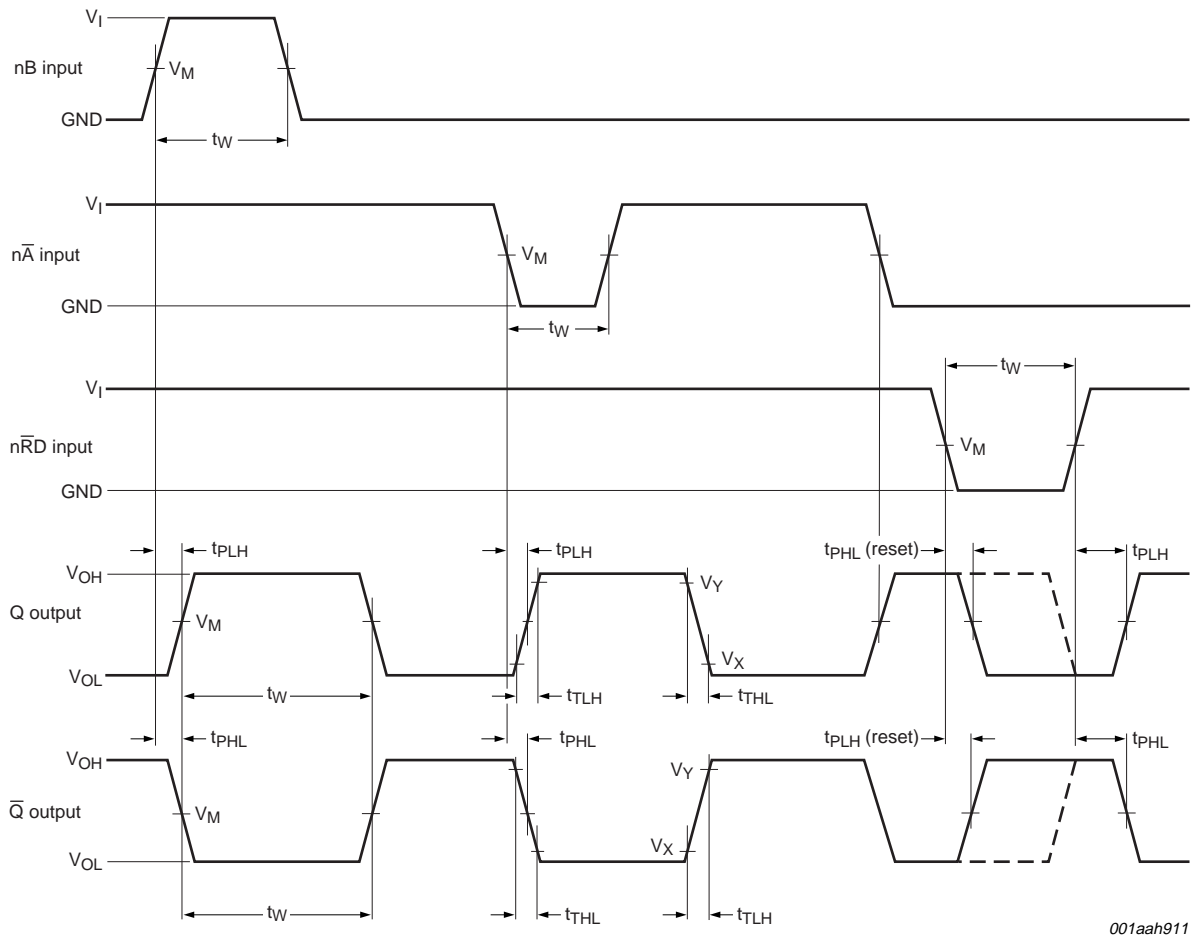
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

∑ (C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms



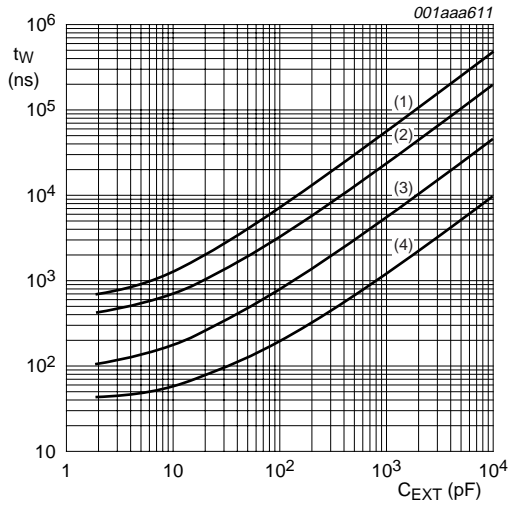
Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Pulse widths, propagation delays from inputs (nA, nB, nRD) to outputs (nQ, nQ) and output transition times

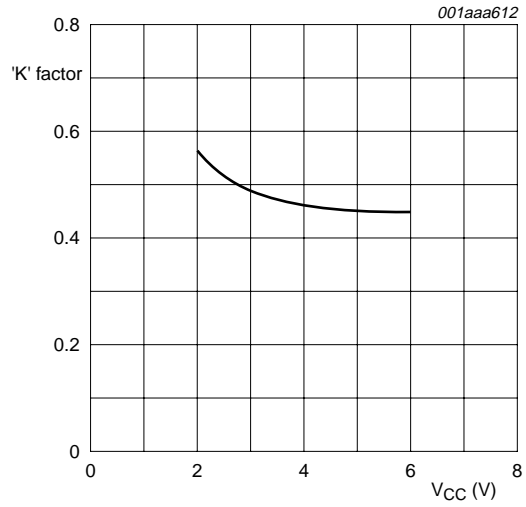
Table 8. Measurement points

| Type | Input | | Output | | |
|----------|----------|-------------|-------------|-------------|-------------|
| | V_I | V_M | V_M | V_X | V_Y |
| 74HC423 | V_{CC} | $0.5V_{CC}$ | $0.5V_{CC}$ | $0.1V_{CC}$ | $0.9V_{CC}$ |
| 74HCT423 | 3 V | 1.3 V | 1.3 V | $0.1V_{CC}$ | $0.9V_{CC}$ |



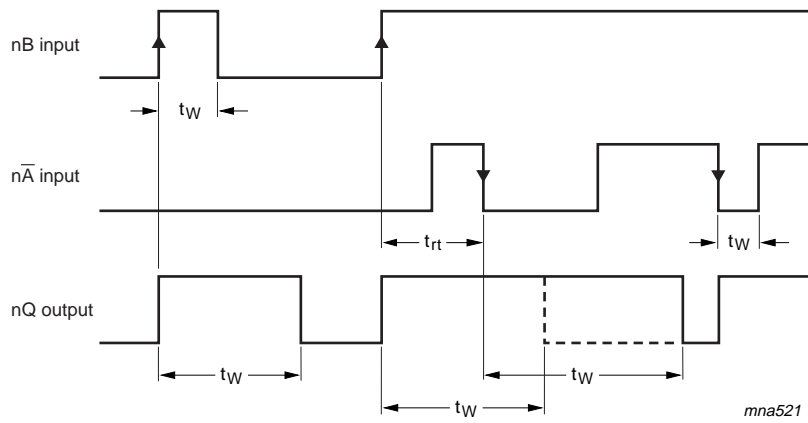
- $V_{CC} = 5.0\text{ V}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (1) $R_{EXT} = 100\text{ k}\Omega$.
 - (2) $R_{EXT} = 50\text{ k}\Omega$.
 - (3) $R_{EXT} = 10\text{ k}\Omega$.
 - (4) $R_{EXT} = 2\text{ k}\Omega$.

Fig 8. Typical output pulse width as a function of the external capacitor values



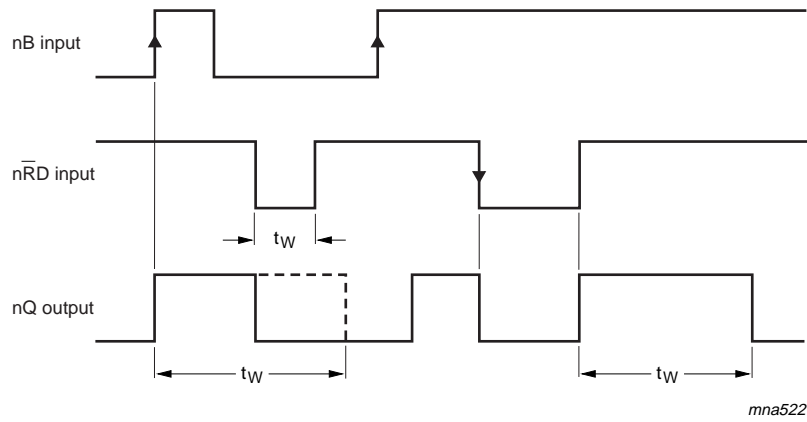
External capacitance = 10 nF,
external resistance = 10 kΩ to 100 kΩ and $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig 9. Typical 'K' factor



$n\overline{RD} = \text{HIGH}$.

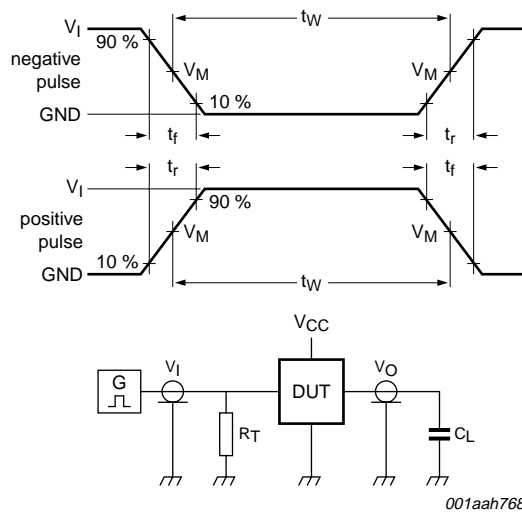
Fig 10. Output pulse control using retrigger pulse (t_{trig})



mna522

n \bar{A} = LOW.

Fig 11. Output pulse control using reset input nRD



001aah768

Test data is given in [Table 9](#).

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

Fig 12. Test circuit for measuring switching times

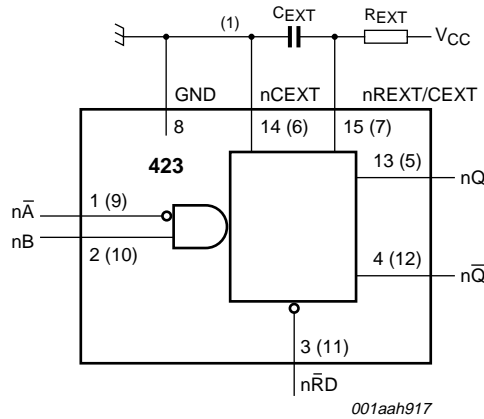
Table 9. Test data

| Supply | Input | Load |
|----------------|----------|--------------|
| V_{CC} | V_I | C_L |
| 2.0 V to 6.0 V | V_{CC} | 15 pF, 50 pF |
| | | t_r, t_f |
| | | 6 ns |

12. Application information

12.1 Timing component connections

The basic output pulse width is essentially determined by the values of the external timing components R_{EXT} and C_{EXT} .



- (1) For minimum noise generation it is recommended that the nCEXT pins (6, 14) are connected to ground externally to the GND pin (8).

Fig 13. Timing component connections

12.1.1 Minimum monostable pulse width

To set the minimum pulse width, when $C_{EXT} < 10$ nF, see [Figure 8](#) and when $C_{EXT} > 10$ nF, the output pulse width is defined as:

$$t_W = 0.45 \times R_{EXT} \times C_{EXT} \text{ (typ.)}, \text{ where:}$$

t_W = pulse width in μs ;

R_{EXT} = external resistor in $\text{k}\Omega$;

C_{EXT} = external capacitor in nF.

12.2 Power-up considerations

When the monostable is powered-up it may produce an output pulse, with a pulse width defined by the values of R_{EXT} and C_{EXT} , this output pulse can be eliminated using the circuit shown in [Figure 14](#).

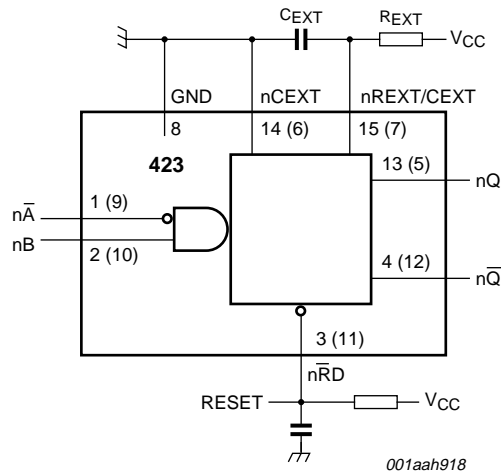


Fig 14. Power-up output pulse elimination circuit

12.3 Power-down considerations

A large capacitor C_{EXT} may cause problems when powering-down the monostable due to the capacitor's stored energy. When a system containing this device is powered-down or a rapid decrease of V_{CC} to zero occurs, the monostable may sustain damage, due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode D_{EXT} preferably a germanium or Schottky type diode able to withstand large current surges and connect as shown in [Figure 15](#).

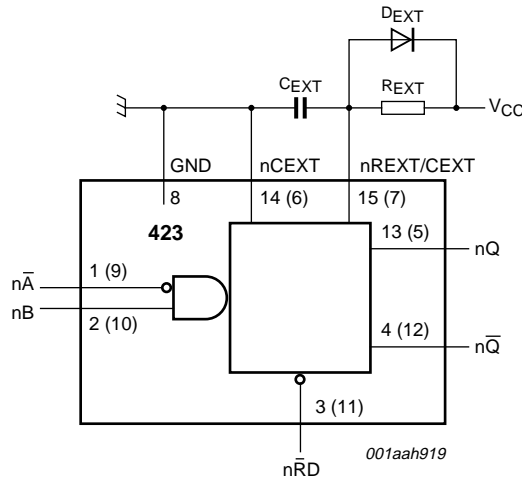


Fig 15. Power-down protection circuit

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

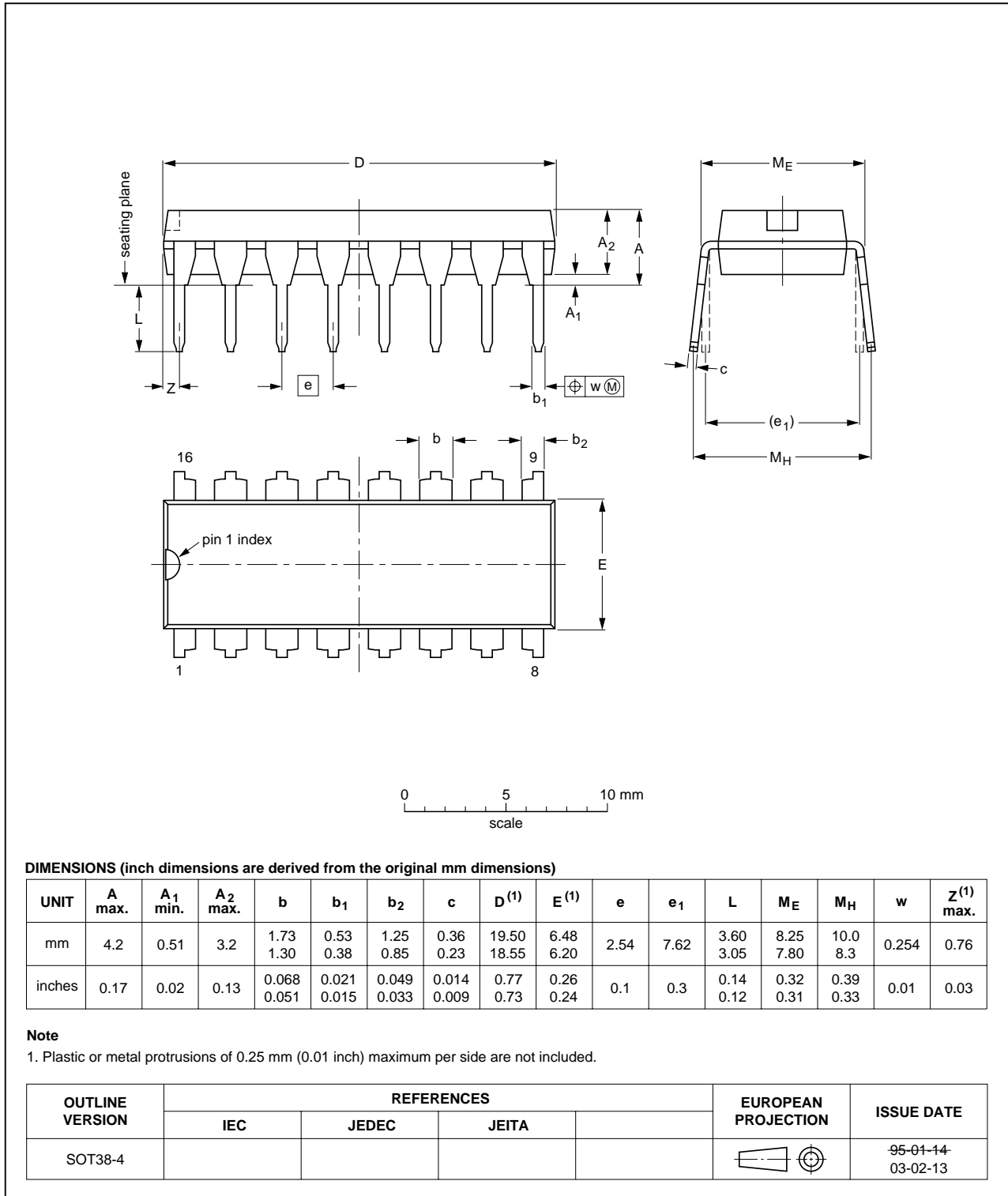


Fig 16. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

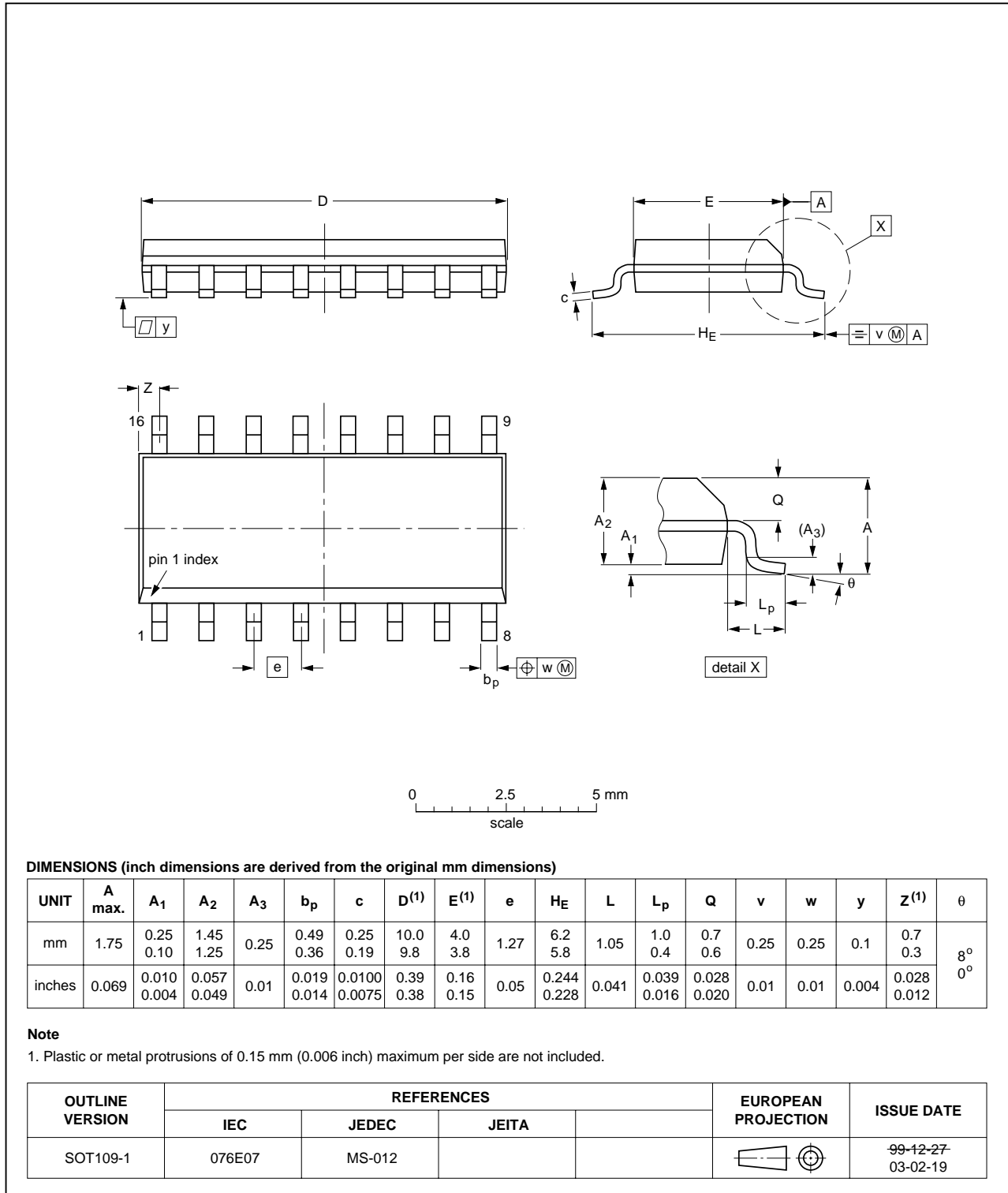


Fig 17. Package outline SOT109-1 (SO16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

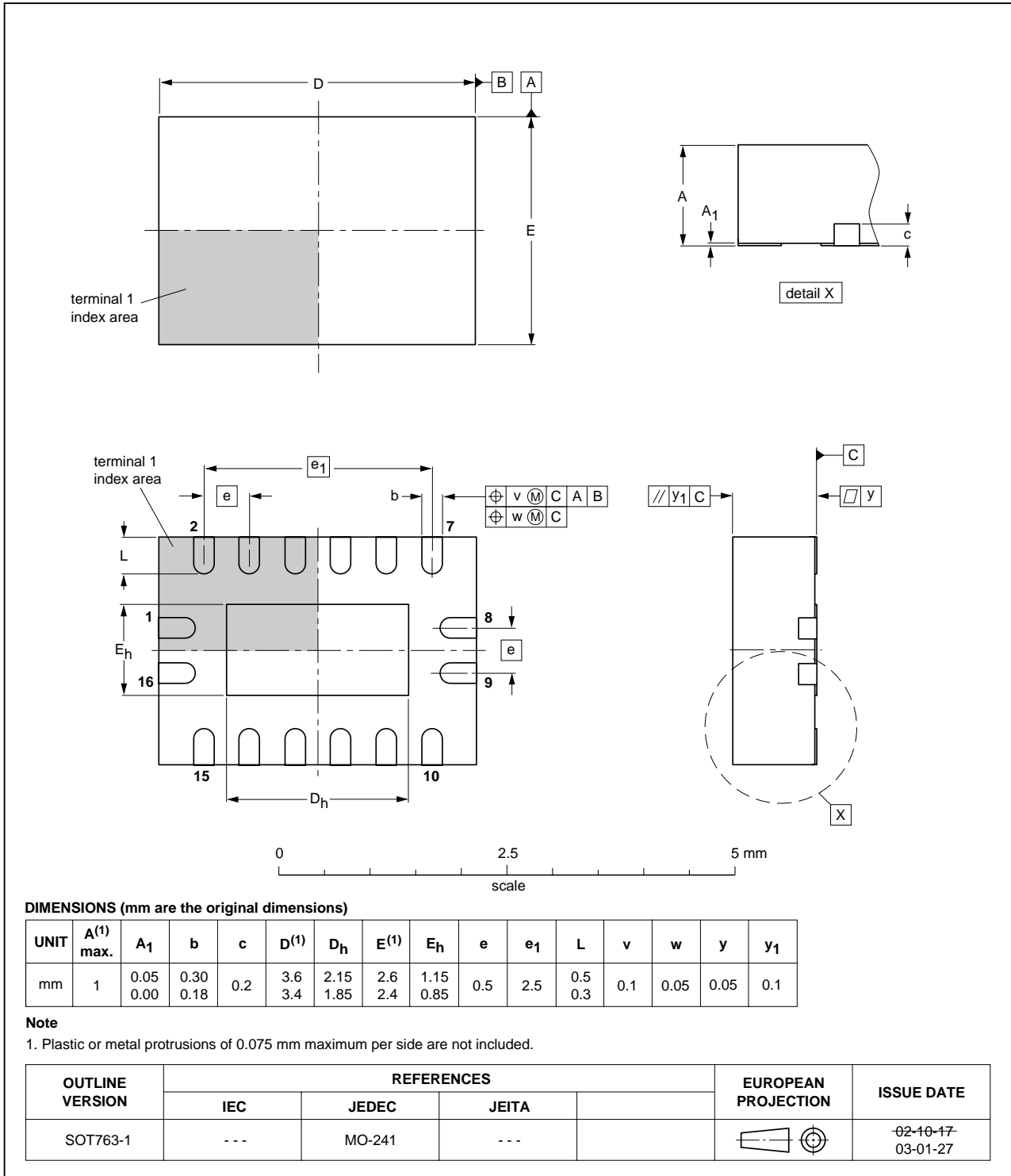


Fig 18. Package outline SOT763-1 (DHVQFN16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

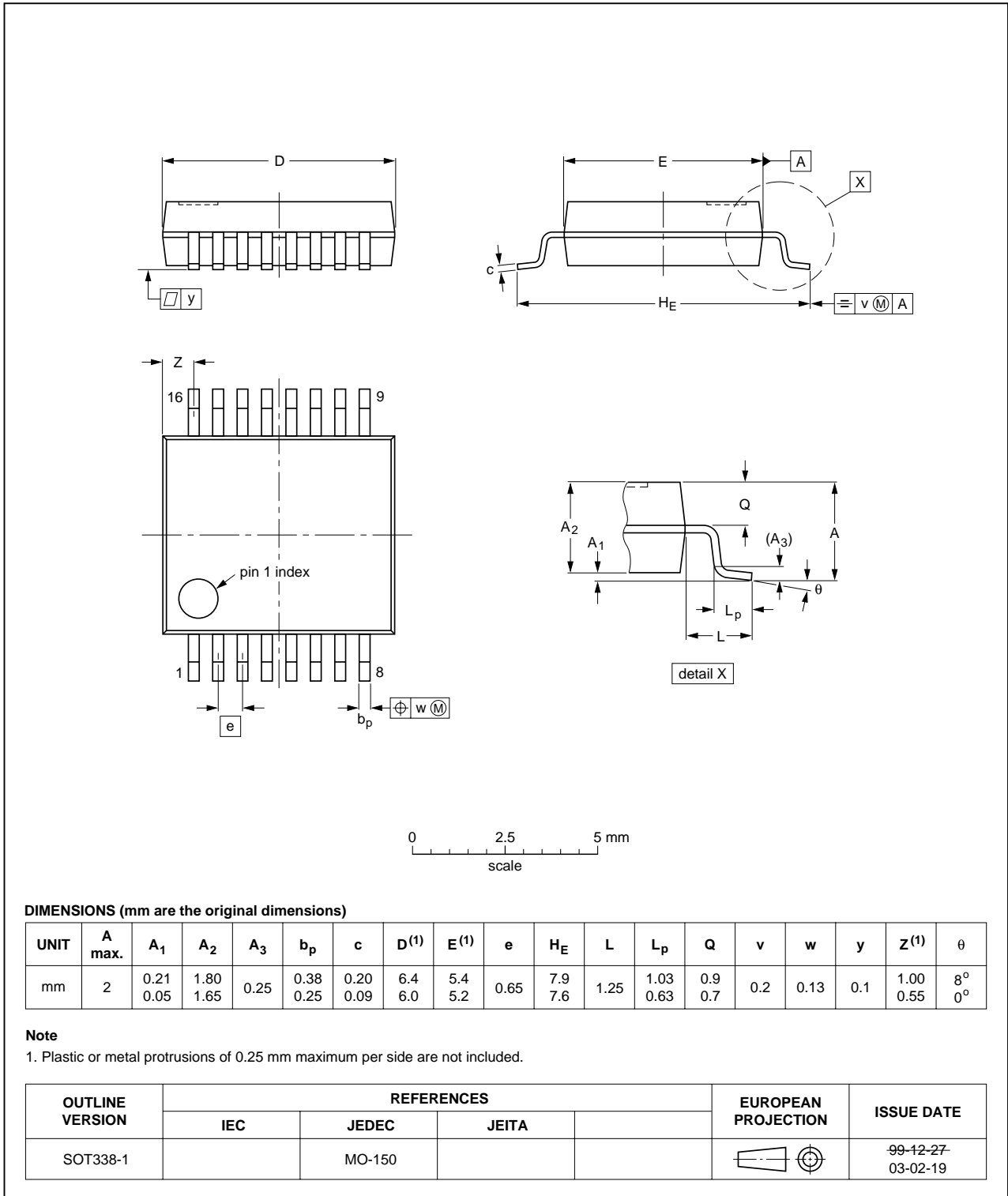


Fig 19. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

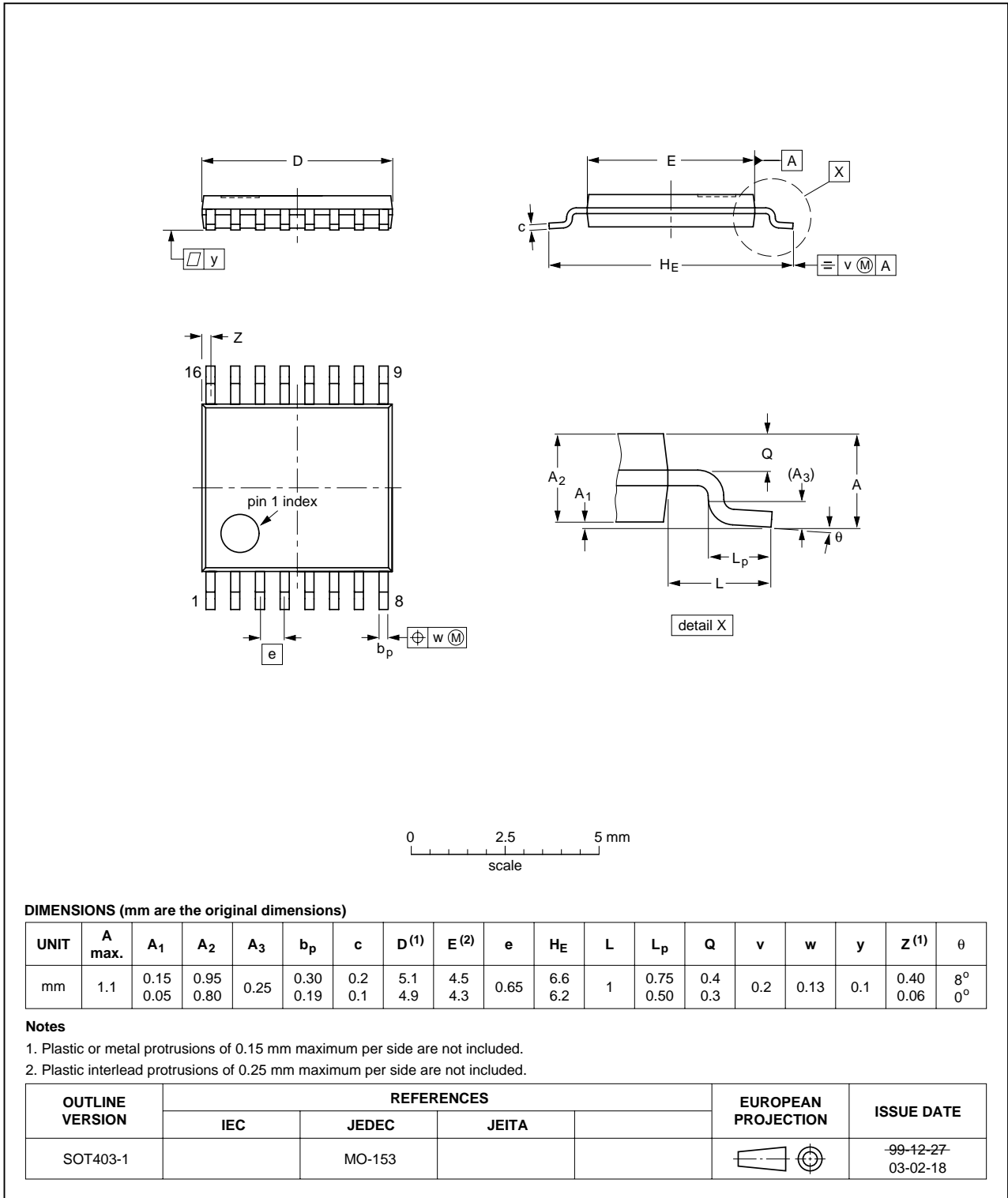


Fig 20. Package outline SOT403-1 (TSSOP16)

14. Abbreviations

Table 10. Abbreviations

| Acronym | Description |
|---------|---|
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |
| TTL | Transistor-Transistor Logic |

15. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------|--------------|--|---------------|-------------------|
| 74HC_HCT423_3 | 20080724 | Product data sheet | - | 74HC_HCT423_CNV_2 |
| Modifications: | | <ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Section 3 "Ordering information", Section 5 "Pinning information" and Section 13 "Package outline", added type numbers 74HC423BQ and 74HCT423BQ (DHVQFN16 package). Figure 4 "Logic diagram", Figure 13 "Timing component connections" and Figure 15 "Power-down protection circuit" redrawn. Section 10 "Dynamic characteristics" C_{PD} values added. Figure 12 "Test circuit for measuring switching times" added. Section 12.1 "Timing component connections" moved to Section 12. Section 14 "Abbreviations" added. | | |
| 74HC_HCT423_CNV_2 | 19980708 | Product specification | - | - |

16. Legal information

16.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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